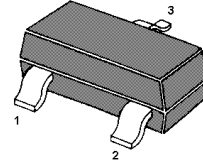


MMBTSC2712

NPN Silicon Epitaxial Planar Transistor

for audio frequency general purpose amplifier applications.

The transistor is subdivided into four groups O, Y, G and L, according to its DC current gain.



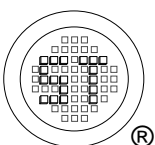
1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_{amb}=25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 2\text{ mA}$	h_{FE}	70	140	-
Current Gain Group O	h_{FE}	120	240	-
Y	h_{FE}	200	400	-
G	h_{FE}	350	700	-
L	h_{FE}			
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	0.25	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	f_T	80	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	3.5	pF



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ISO/TS 16949 : 2009
Certificate No. 180713000



ISO14001 : 2004
Certificate No. 7116



ISO 9001 : 2008
Certificate No. 50713410



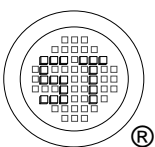
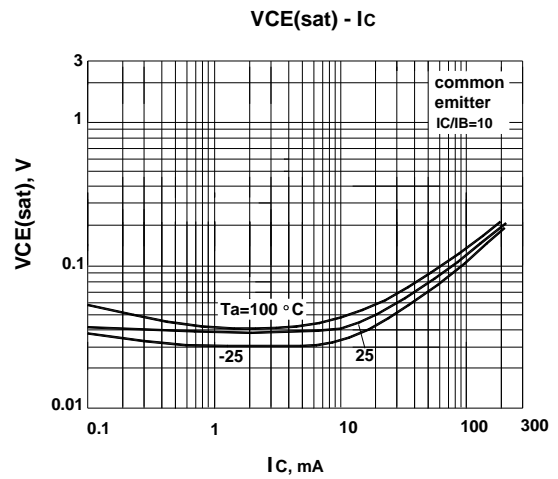
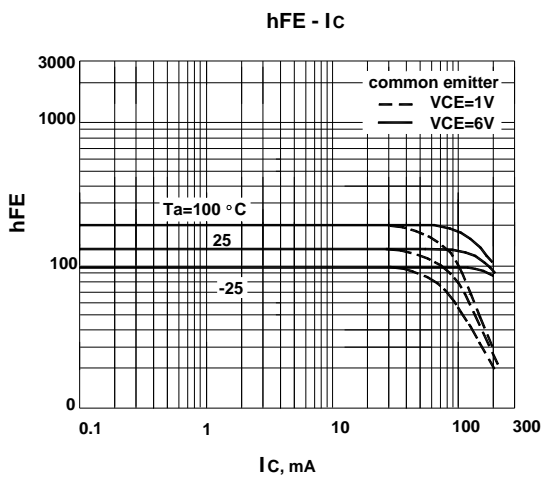
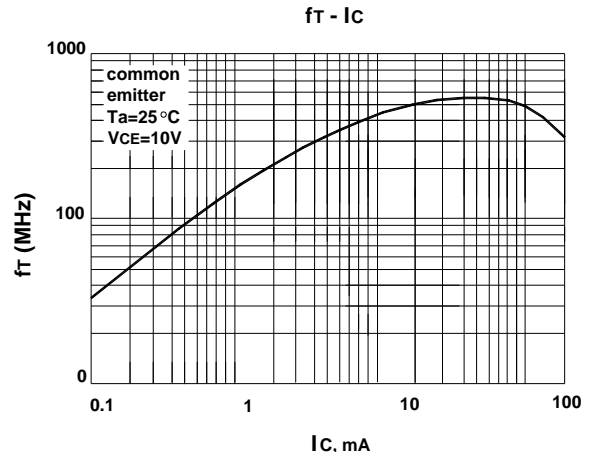
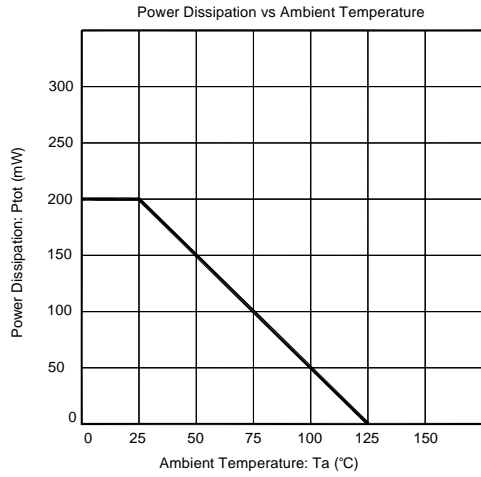
BS-OHSAS 18001 : 2007
Certificate No. 7116



IECQ QC 080000
Certificate No. PRC:SPM-1483-1

Dated: 16/03/2015 Rev: 01

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